

DUAL N/P CHANNEL MOSFET, 25V, Transistor Polarity:N and P Channel, Continuous Drain Current Id:500mA, Drain Source Voltage Vds:25V, On Resistance Rds(on):450mohm, Rds(on) Test Voltage Vgs:4.5V, Threshold Voltage Vgs:800mV

Manufacturers	ON Semiconductor, LLC
Package/Case	SC-70-6
Product Type	Transistors
RoHS	Green
Lifecycle	



Images are for reference only

Please submit RFQ for FDG6321C or [Email to us: sales@ovaga.com](mailto:sales@ovaga.com) We will contact you in 12 hours.

[RFQ](#)

General Description

These dual N & P-Channel logic level enhancement mode field effect transistors are produced using a proprietary, high cell density, DMOS technology. This very high density process is especially tailored to minimize on-state resistance. This device has been designed especially for low voltage applications as a replacement for bipolar digital transistors and small signal MOSFETS. Since bias resistors are not required, this dual digital FET can replace several different digital transistors, with different bias resistor values.

Features

N-Ch 0.50 A, 25 V = 0.60 Ω @>

P-Ch -0.41 A, -25 V = 1.5 Ω @>

Application

ONSEMI

Related Products



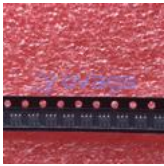
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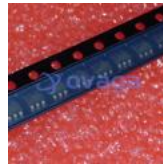
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